Distributed Gate Thyristor Type SA10AP1331EA



Contact us!

Date: September, 2020 Data Sheet Issue: 1



	ORDERING INFORMATION			(Please quote 12 to 15 digit code as below)			
SA	10	AP	1331	Е	А		
-	Voltage Code	Outline Code	Current code	Type code	t _q code	Optional code	
t _q code: A = 10μs, B = 12μs, C = 15μs, D = 20μs							

Find more!



Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{DRM}	Repetitive peak off-state voltage, (note 1)	1000	V
V_{DSM}	Non-repetitive peak off-state voltage, (note 1)	1000	V
V_{DDC}	Maximum DC of-state voltage, (note 1)	700	V
V_{RRM}	Repetitive peak reverse voltage, (note 1)	1000	V
V _{RSM}	Non-repetitive peak reverse voltage, (note 1)	1100	V
V_{RDC}	Maximum DC revrese voltage, (note 1)	700	V
note 1)	De-rating factor of 0.13%/°C is applicable for T_j below 25°C		

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
I _{T(AV)M}	Maximum average on-state current, T _{sink} = 55°C, (note 1)	1331	А
$I_{T(AV)M}$	Maximum average on-state current, T _{sink} = 85°C, (note 1)	878	А
$I_{T(AV)M}$	Maximum average on-state current, T _{sink} = 85°C, (note 2)	503	А
I _{T(RMS)}	Nominal RMS on-state current, T _{sink} = 25°C (note 1)	2687	А
I _{T(d.c.)}	D.C. on-state current, T _{sink} = 25°C, (note 3)	9191	А
I _{TSM}	Peak non-repetitive surge current t_p = 10ms, V_{RM} = 60% V_{RRM} , (note4)	18.2	kA
I _{TSM2}	Peak non-repetitive surge current t_p = 10ms, $V_{RM} \le$ 10V, (note 4)	20.2	kA
l ² t	I^2 t capacity for fusing $t_p = 10$ ms, $V_{RM} = 60\%V_{RRM}$, (note 4)	$1.66 \cdot 10^6$	A^2s
I ² t	$\rm I^2t$ capacity for fusing $\rm t_p$ = 10ms, $\rm V_{RM} \le 10V$, (note 4)	2.0 · 10 ⁶	A^2s
(di/dt) _{cr}	Critical rate of rise of on-state current (repetitive), (note 5)	1000	A/µs
(di/dt/cr	Critical rate of rise of on-state current (non repetitive), (note 5)	1500	A/µs
V_{RGM}	Peak reverse gate voltage	5	V
$P_{G(AV)}$	Mean forward gate power	5	W
P_{GM}	Peak forward gate power	30	W
T _{jop}	Operating temperature range	-40 to +125	°C
T _{stg}	Storage temperature range	-40 to +150	°C
note 1)	Double-side cooled, single phase, 50Hz, 180° half-sinewave.		
note 2)	Single-side cooled, single phase, 50Hz, 180° half-sinewave.		
note 3)	Double-side cooled		
note 4)	Half-sinewave, 125°C T _j initial		
note 5)	V _D = 67%V _{DRM} , I _{FG} = 2A, t _R ≤ 0.5μs, T _{case} = 125°C		



Characteristics

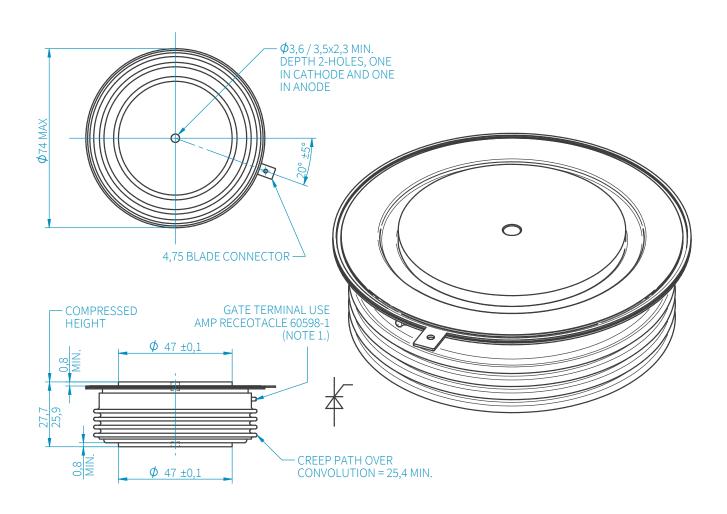
	PARAMETER	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
V_{TM}	Maximum peak on-state voltage	I _{TM} = 2000A	-	-	2.02	V
	Maximum peak on-state voltage	I _{TM} = 3900A	-	-	2.5	V
V_{T0}	Threshold voltage		-	-	1.45	V
r_{T}	Slope resistance		-	-	0.285	mΩ
(dv/dt) _{CR}	Critical rate of rise of off-state voltage	V _D = 80%V _{DRM} , Linear ramp, Gate o/c	200	-	-	V/µs
I _{DRM}	Peak off-state current	Rated V _{DRM}	-	-	150	mA
I _{RRM}	Peak reverse current	Rated V _{RRM}	-	-	150	mA
V_{GT}	Gate trigger voltage	$T_j = 25^{\circ}C, V_D = 10V, I_T = 3A$		-	3.0	V
I_{GT}	Gate trigger current			-	300	mA
V_{GD}	Gate non-trigger voltage	Rated V _{DRM}	-	-	0.25	V
I_{H}	Holding current	T _j = 25°C	-	-	1000	mA
t_{GD}	Gate controlled turn-on delay time	$V_D = 67\%V_{DRM}$, $I_{TM} = 1000A$, $di/dt = 60A/\mu s$,	-	0.5	1.0	μs
t _{GT}	Turn-on time	$I_{FG} = 2A$, $t_r = 0.5 \mu s$, $T_j = 25$ °C		1.0	2.0	μs
Q_{RR}	Recovered charge		-	200	-	μC
Q_{RA}	Recovered charge, 50% Chord	$I_{TM} = 1000A$, $t_p = 1000\mu s$, $di/dt = 60A/\mu s$,	-	80	100	μC
I _{RM}	Reverse recovery current $V_R = 50V$		-	70	-	А
t _{RR}	Reverse recovery time			2.2	-	μs
1	Turn-off time (note 2)	I_{TM} = 1000A, t_p = 1000 μ s, di/dt = 60A/ μ s, V_R = 50V, V_{DR} = 33% V_{DRM} , d V_{DR} /dt = 20V/ μ s	-	10	15	μs
t _{GQ}		$\begin{split} &I_{TM} = 1000\text{A}, t_p = 1000\mu\text{s}, \text{di/dt} = 60\text{A}/\mu\text{s}, \\ &V_R = 50\text{V}, V_{DR} = 33\%\text{V}_{DRM}, \text{dV}_{DR}/\text{dt} = 200\text{V}/\mu\text{s} \end{split}$	-	15	20	μs
R_{thJK}	Thermal resistance, junction to sink	Double-side cooled	-	-	0.022	K/W
rtnJK	(note 3)	Single-side cooled	-	-	0.044	K/W
F	Mounting force	(note 3)	19	-	26	kN
W _t	Weight		-	510	-	g
note 1)	Unless otherwise indicated $T_j = 125$ °C					
note 2)	The required t_Q (specified with dV_{DR}/dt = 200V/ μ s) is 10 μ s					
note 3)	For other clamp forces, please consult factory					

Request full technical data sheet via e-mail, free of charge:

Order Now!



Outline Drawing



SANCONA®

technical solutions

SANCONA GmbH

An der Hebemärchte 26 D-04316 Leipzig // Registry Court: Leipzig HRB 32946 VAT Reg No.: DE308741810

Tax number: 232/118/085686

The information contained herein is confidential and is protected by Copyright. The information may not be used or disclosed except with written permission of and in the manner permitted by the proprietors SANCONA GmbH. In the interest of product improvement, SANCONA reserves the right to change specifications at any time without prior notice. Devices with a suffix code (2-letter, 3-letter or letter/digit/letter combination) added to their generic code are not necessarily subject to the conditions and limits contained in this report.

©SANCONA GmbH